

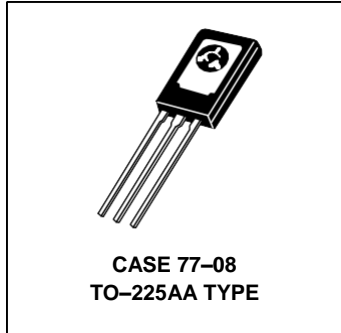
TECHNICAL DATA

... designed for use in line-operated applications such as low power, line-operated series pass and switching regulators requiring PNP capability.

- High Collector-Emitter Sustaining Voltage —
 $V_{CEO(sus)} = 300 \text{ Vdc @ } I_C = 1.0 \text{ mAdc}$
- Excellent DC Current Gain —
 $h_{FE} = 30 - 240 @ I_C = 50 \text{ mAdc}$
- Plastic Thermopad Package



**0.5 AMPERE
 POWER TRANSISTOR
 PNP SILICON
 300 VOLTS
 20 WATTS**



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	300	Vdc
Emitter-Base Voltage	V_{EB}	3.0	Vdc
Collector Current — Continuous	I_C	500	mAdc
Total Power Dissipation @ $T_C = 25 \text{ C}$ Derate above 25 C	P_D	20 0.16	Watts W/ C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	- 65 to + 150	C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θ_{JC}	6.25	C/W

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	$V_{CEO(sus)}$	300	—	Vdc
Collector Cutoff Current ($V_{CB} = 300 \text{ Vdc}, I_E = 0$)	I_{CBO}	—	100	μAdc
Emitter Cutoff Current ($V_{EB} = 3.0 \text{ Vdc}, I_C = 0$)	I_{EBO}	—	100	μAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 50 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$)	h_{FE}	30	240	—
---	----------	----	-----	---

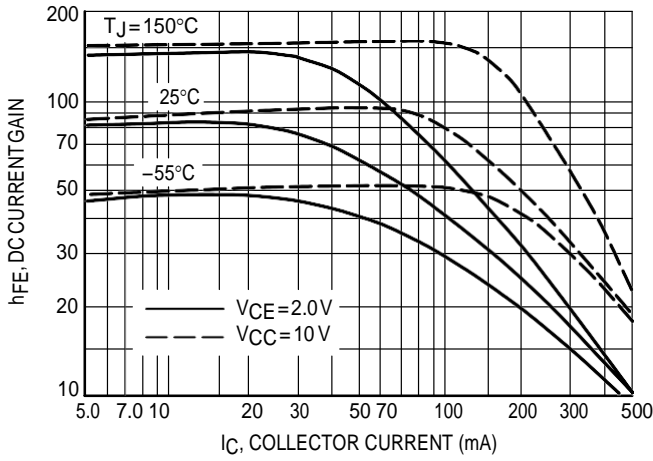


Figure 1. DC Current Gain

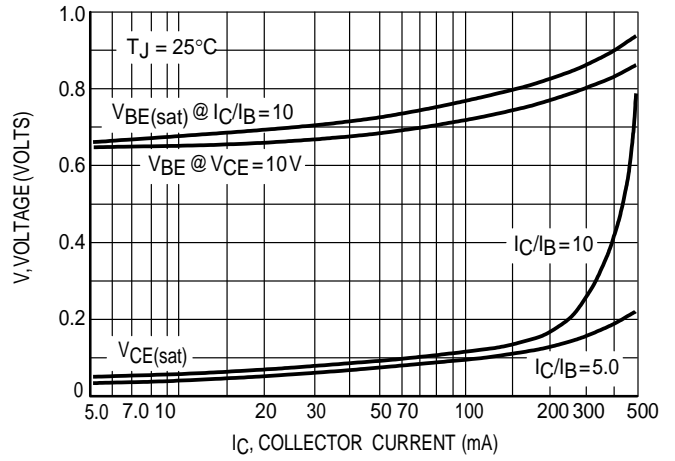


Figure 2. "On" Voltages

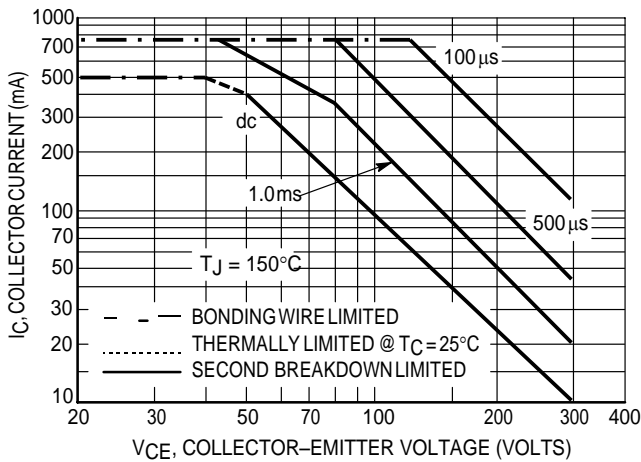


Figure 3. Active-Region Safe Operating Area

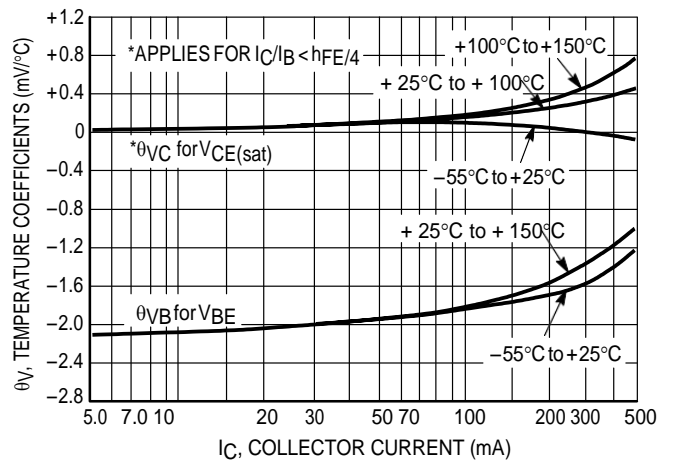


Figure 4. Temperature Coefficients

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 3 is based on $T_{J(pk)} = 150\text{ C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} = 150\text{ C}$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

The data of Figure 3 is based on $T_{J(pk)} = 150\text{ C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} = 150\text{ C}$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

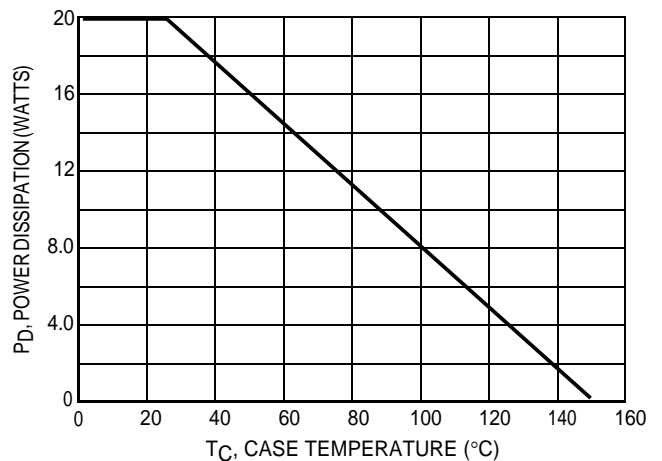
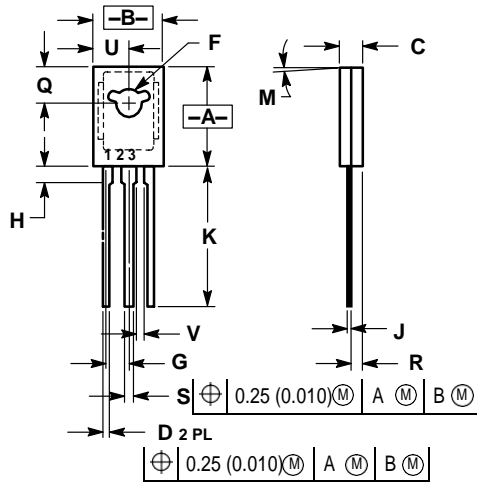


Figure 5. Power Derating

PACKAGE DIMENSIONS



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5 TYP		5 TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.055	1.15	1.39
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	—	1.02	—

STYLE 1:

- PIN 1. EMITTER
2. COLLECTOR
3. BASE

**CASE 77-08
TO-225AA TYPE
ISSUE V**

